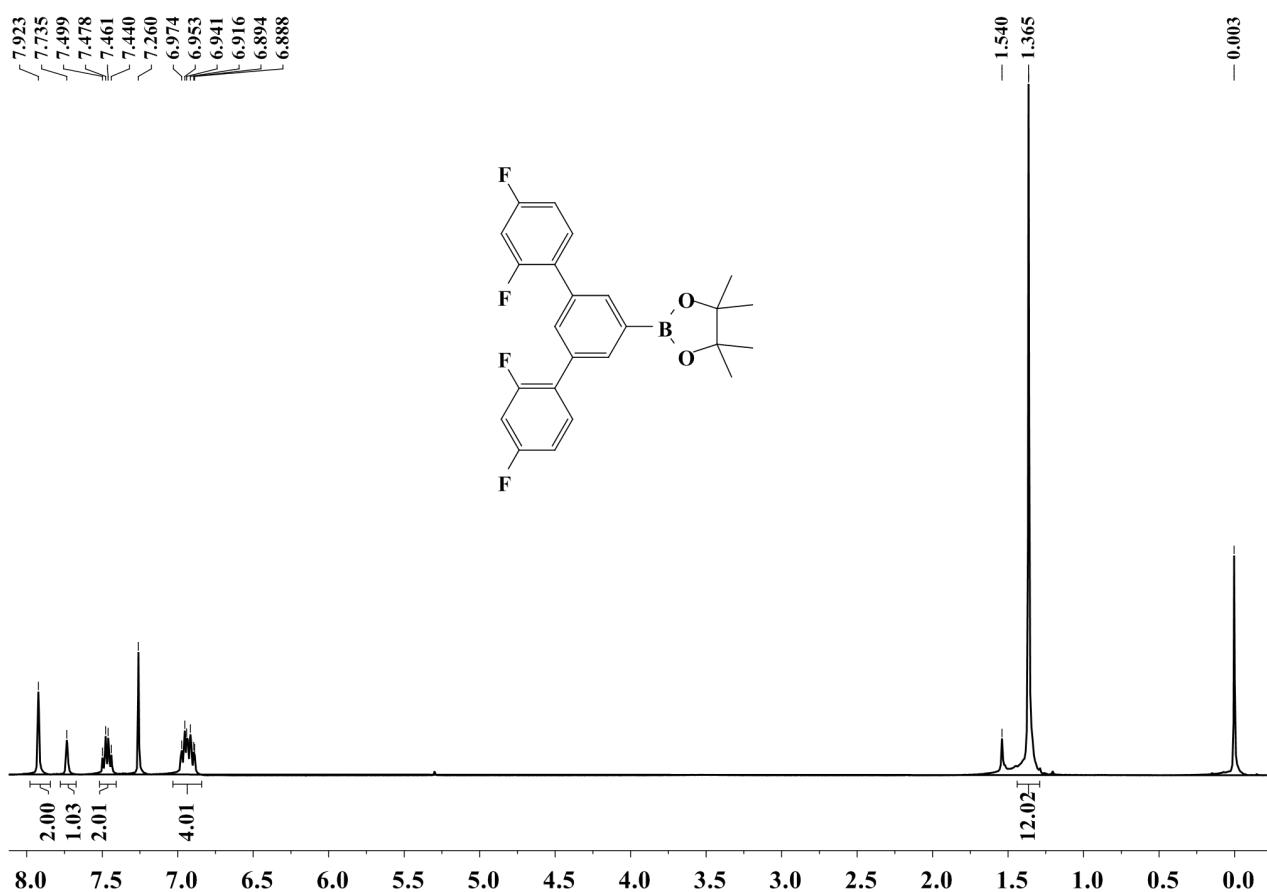


*Electronic Supplementary Information*

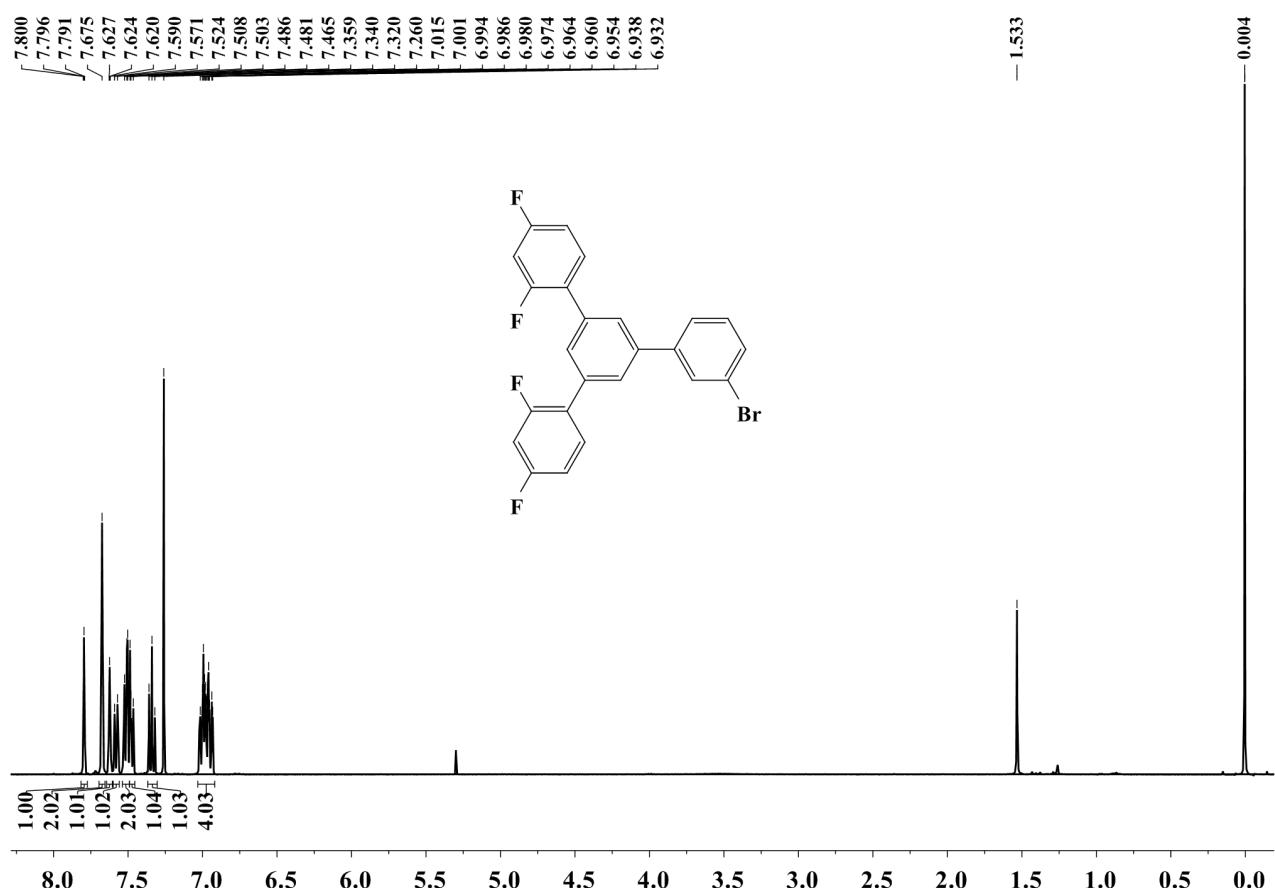
**High  $T_g$  Small-Molecule Phenanthroline Derivatives as a Potential Universal Hole-Blocking Layer for High Power-Efficiency and Stable Organic Light-Emitting Diodes**

Xin-Feng Wei, Wan-Yi Tan, Jian-Hua Zou, Qing-Xun Guo, Dong-Yu Gao, Dong-Ge Ma, Junbiao Peng, Yong Cao, and Xu-Hui Zhu\*

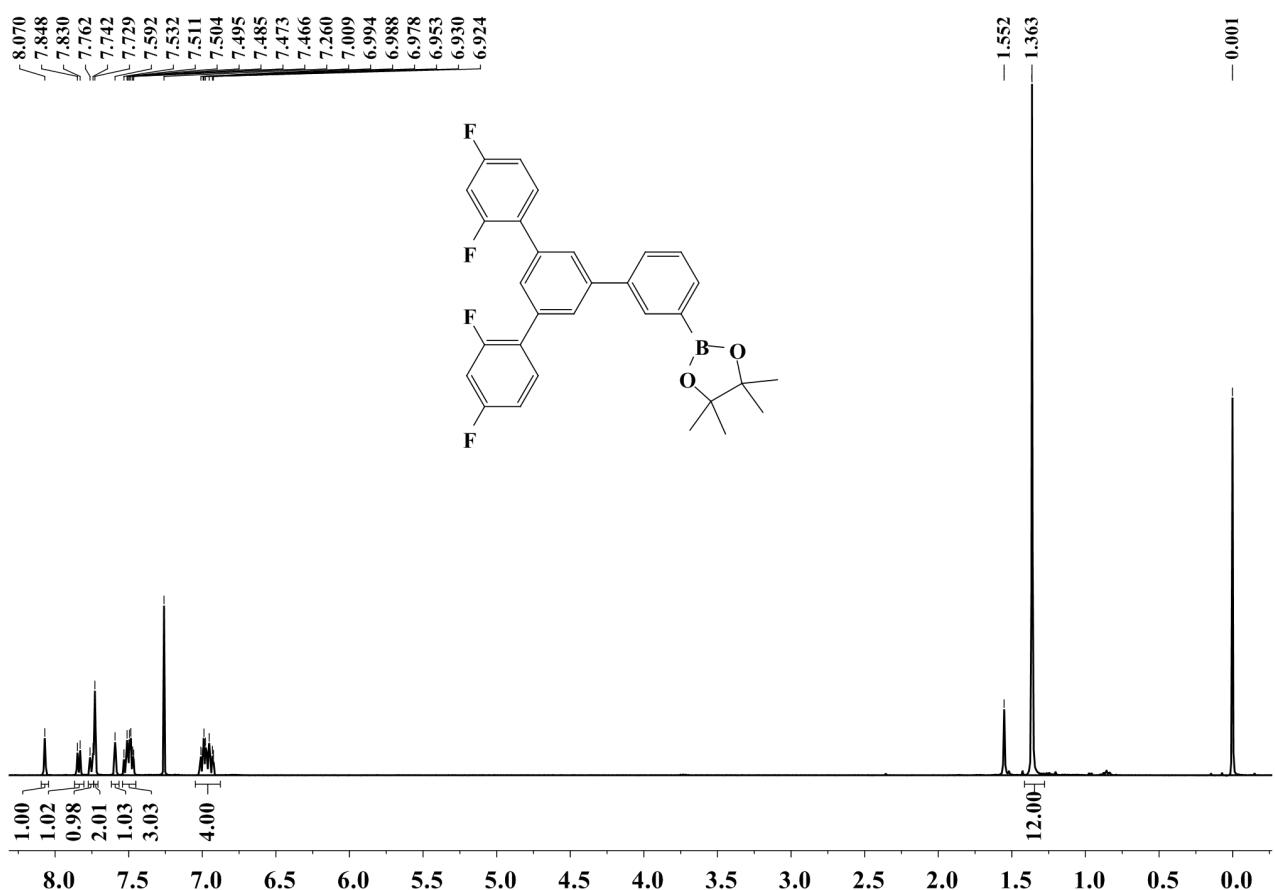
**Fig. S1-1**  $^1\text{H}$  NMR of compound **2** ( $\text{CDCl}_3$ , 400 MHz).



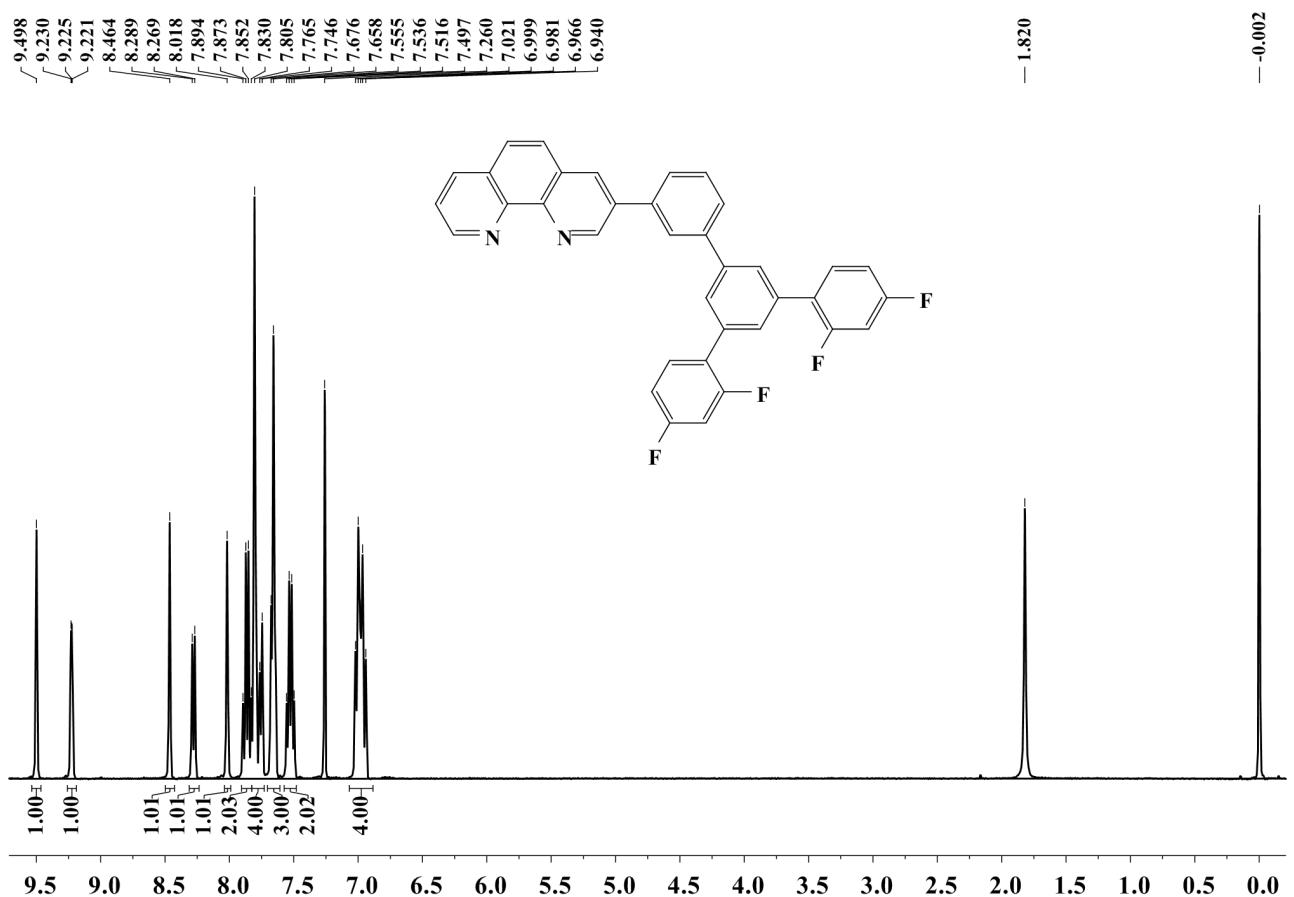
**Fig. S1-2**  $^1\text{H}$  NMR of compound **3** ( $\text{CDCl}_3$ , 400 MHz).



**Fig. S1-3**  $^1\text{H}$  NMR of compound **4** ( $\text{CDCl}_3$ , 400 MHz).



**Fig. S1-4**  $^1\text{H}$  NMR of Phen-DFP ( $\text{CDCl}_3$ , 400 MHz).



**Fig. S2** Microanalysis data of compound **Phen-DFP**: provided by the Instrumental Analysis & Research Center, Sun Yat-Sen University, Guangzhou, China

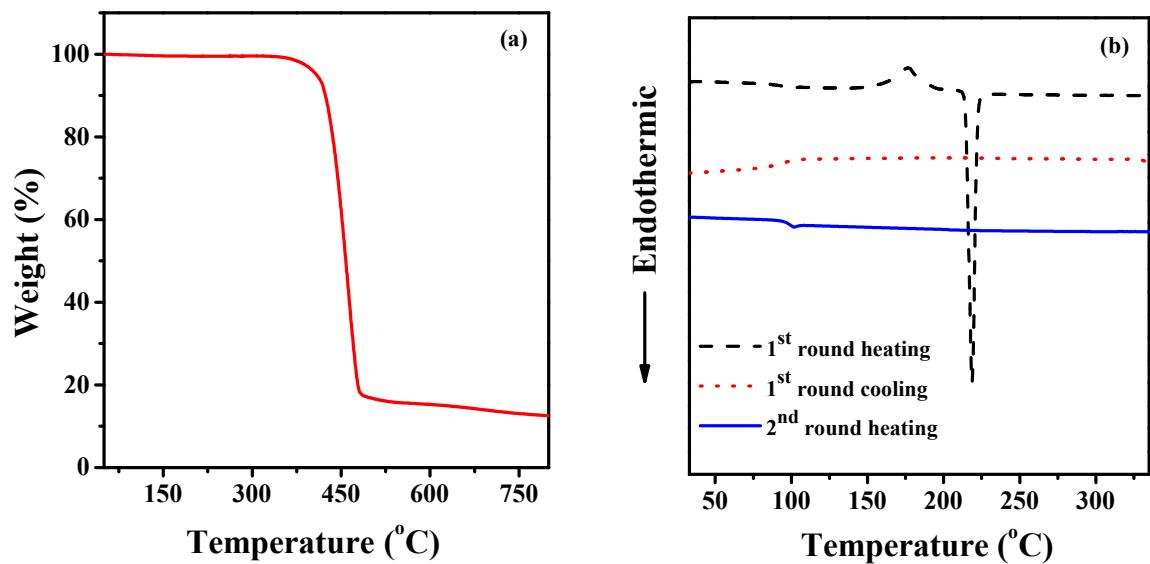
Document: 20160426 CHN test (varioELcube) from: 2016/4/27 7:55:12

CHN元素含量分析  
varioELcube CHNS/O 元素分析仪  
serial number: 19152014

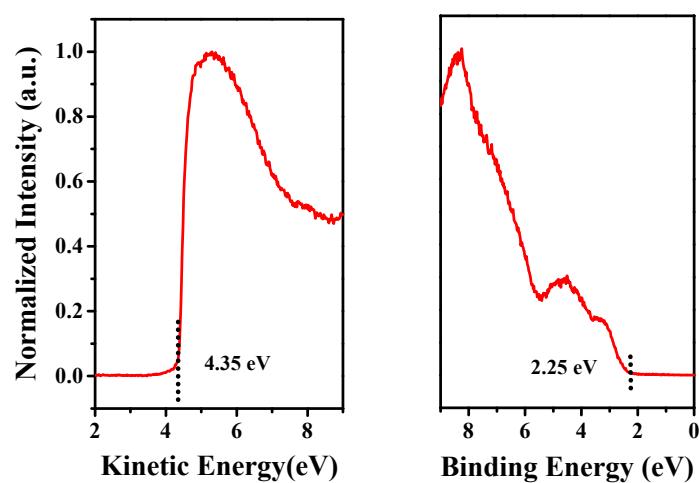
**Text report**

No.	Name	Weight [mg]	C [%]	H [%]	N [%]	C/N ratio	C/H ratio	Date	Time
93	Phen-DFP	1.9920	77.37	3.717	4.91	15.7495	20.8156	26.04.2016	22:11

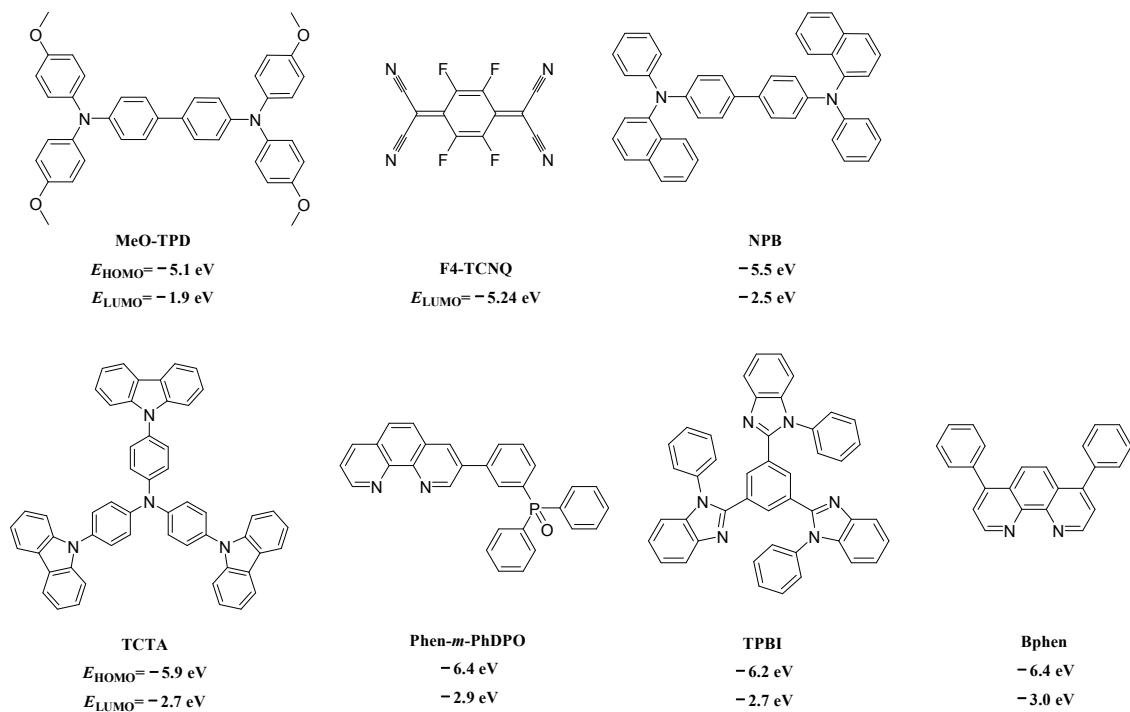
**Fig. S3** (a) Thermogravimetric analysis and (b) DSC diagrams of **Phen-DFP**.



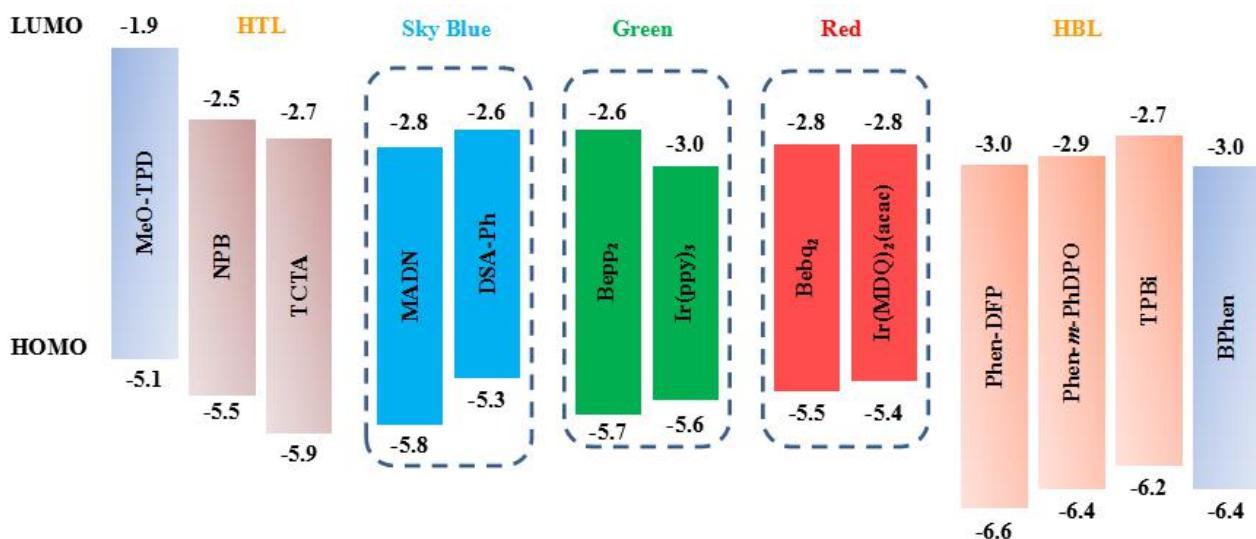
**Fig. S4** UPS spectrum at the low-kinetic energy part (a) and valence band spectrum near the Fermi level (b) for **Phen-DFP** (10 nm) on the ITO surface.



**Fig. S5** The chemical structures of the organic charge-transport materials involved in the sky blue FLOLEDs, green and red PHOLEDs with their HOMO and LUMO levels, as well as the *p*-type dopant F4-TCNQ.

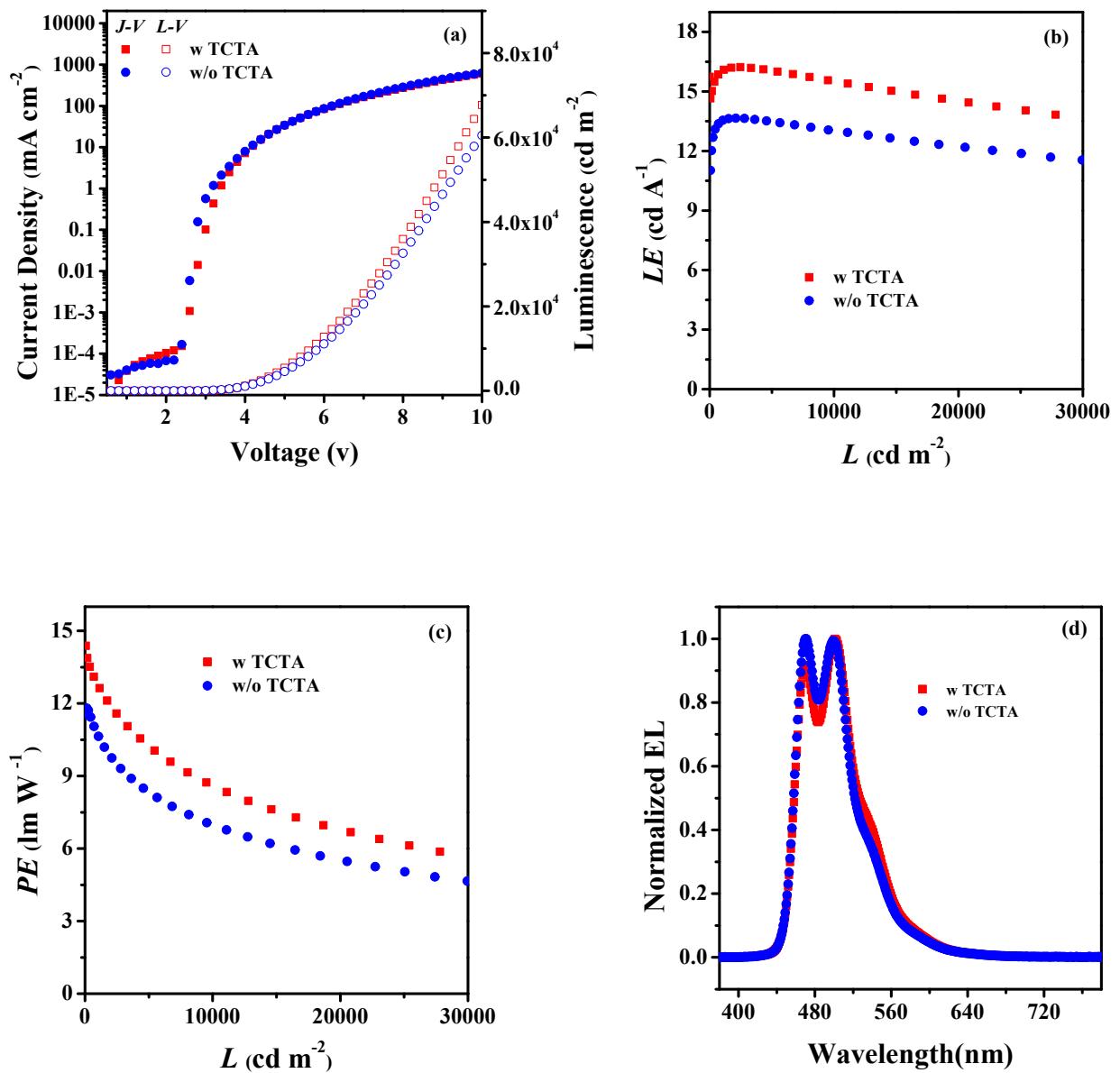


**Fig. S6** The energy diagrams of the *pin* OLEDs



**Fig. S7** EL characteristics of **Phen-DFP** based sky blue FLOLEDs with (w) and without (w/o) a TCTA layer: (a)  $J-V-L$ , (b)  $LE-L$ , (c)  $PE-L$  and (d) EL spectra.

- ❖ ITO/MeO-TPD:F4-TCNQ(100 nm, 4%)/**NPB(20 nm)**/MADN:7%DSA-Ph (30 nm)/**Phen-DFP** (10 nm)/Bphen:Cs<sub>2</sub>CO<sub>3</sub>(20 nm, 50%)/Al(200 nm)
- ❖ ITO/MeO-TPD:F4-TCNQ(100 nm, 4%)/**NPB(15 nm)**/TCTA(**5 nm**) /MADN:7%DSA-Ph (30 nm)/**Phen-DFP**(10 nm)/Bphen:Cs<sub>2</sub>CO<sub>3</sub>(20 nm, 50%)/Al(200 nm)



**Table S1** Summary of the Electroluminescent dada

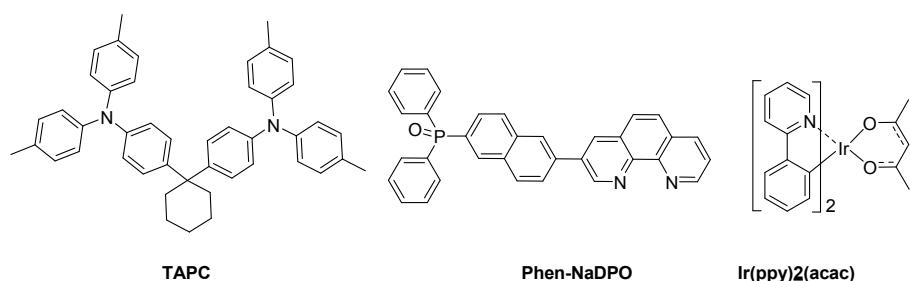
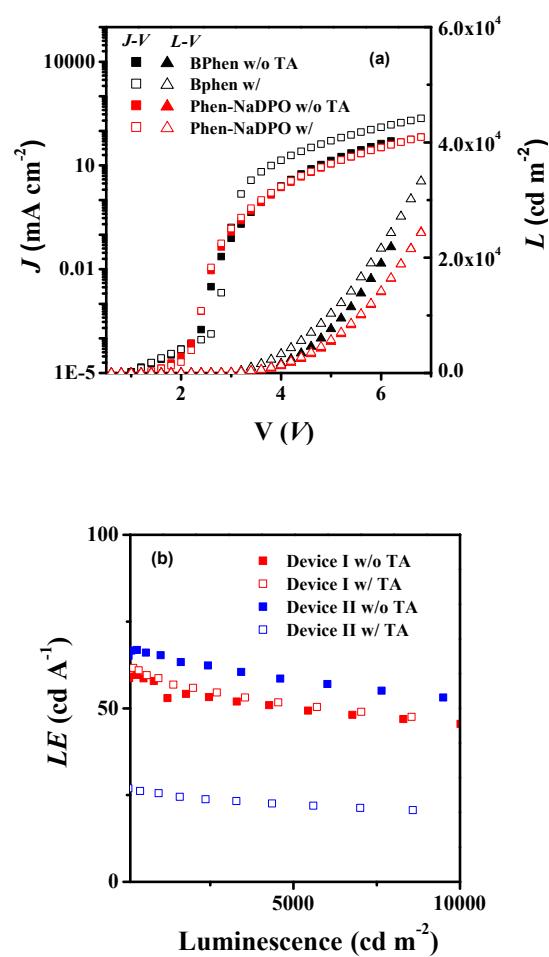
HBL	Sky Blue FLOLEDs	V <sub>on</sub> <sup>a)</sup> [v]	@100 cd m <sup>-2</sup>			@1000 cd m <sup>-2</sup>			EQE [%]
			LE [cd A <sup>-1</sup> ]	PE [lm W <sup>-1</sup> ]	V [v]	J [mA cm <sup>-2</sup> ]	LE [cd A <sup>-1</sup> ]	PE [lm W <sup>-1</sup> ]	
<b>Phen-DFP</b>	w/ TCTA	2.8	14.8	14.2	3.9	6.2	16.0	12.8	7.2
	w/o TCTA	2.8	11.5	11.7	4.0	7.7	13.5	10.7	6.5
<b>Phen-<i>m</i>-PhDPO</b>	w/ TCTA	2.8	14.2	13.9	3.8	6.3	15.8	13.0	7.2
	w/o TCTA <sup>b)</sup>	2.8	8.9	8.2	4.0	8.9	11.4	8.9	5.4
<b>TPBI</b>	w/ TCTA	2.8	13.7	14.0	3.9	6.2	16.1	13.1	7.4
	w/o TCTA <sup>b)</sup>	3.0	9.8	7.0	5.4	10.0	10.6	6.2	5.09

<sup>a)</sup>At a luminescence of ~1-3 cd m<sup>-2</sup><sup>b)</sup> Data cited from [Ref. 1]

**Fig. S8**  $J-V-L$  (a) and  $LE-L$  (b) characteristics of the green PHOLEDs (ITO/MoO<sub>3</sub>/TAPC:MoO<sub>3</sub> (45 nm, 15%)/ TAPC(15 nm)/TCTA:Ir(ppy)<sub>2</sub>(acac)(20 nm, 8%)/HBL(10 nm)/ETL:Li<sub>2</sub>CO<sub>3</sub>(40 nm, x%)/Li<sub>2</sub>CO<sub>3</sub>(1 nm)/Al): without (solid square) and with (hollow square) thermal annealing (TA) at 80 °C for 15 min.

**Device I:** HBL = **Phen-*m*-PhDPO**, ETL = **Phen-NaDPO**, 5% Li<sub>2</sub>CO<sub>3</sub>

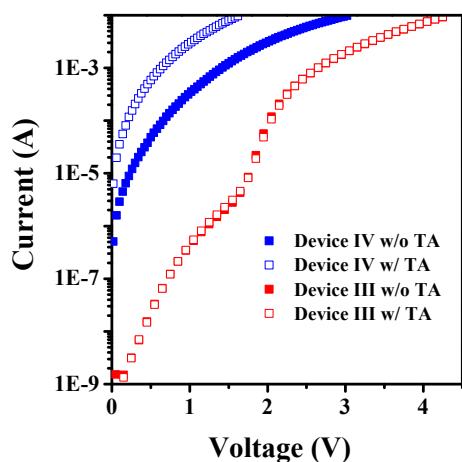
**Device II:** HBL = BPhen, ETL = BPhen, 3% Li<sub>2</sub>CO<sub>3</sub>



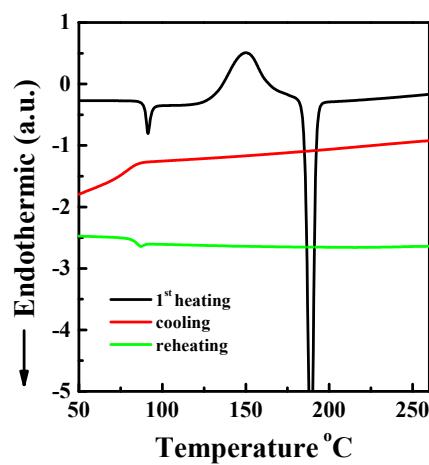
**Fig. S9**  $J-V$  characteristics of the electron-only devices: ITO/HBL(10 nm)/ETL:Li<sub>2</sub>CO<sub>3</sub>(70 nm, x%)/Li<sub>2</sub>CO<sub>3</sub>(1 nm)/Al, without (solid square) and with (hollow square) thermal annealing (TA) at 80 °C for 15 min.

**Device III:** HBL= **Phen-*m*-DPO**, ETL = **Phen-NaDPO**, 5% Li<sub>2</sub>CO<sub>3</sub>

**Device IV:** HBL = ETL = BPhen, 3% Li<sub>2</sub>CO<sub>3</sub>



**Fig. S10.** DSC diagrams of TAPC.



## Reference

[1] W.-Y. Tan, J.-H. Zou, D.-Y. Gao, J.-Z. Liu, N.-N. Chen, X.-H. Zhu, J. B. Peng and Y. Cao, *Adv. Electron. Mater.*, 2016, **2**, 1600101.